

**PNP Silicon Epitaxial Planar Transistor**

for switching and amplifier applications.

As complementary types the NPN transistors 2N3903 and 2N3904 are recommended.

On special request, these transistors can be manufactured in different pin configurations.

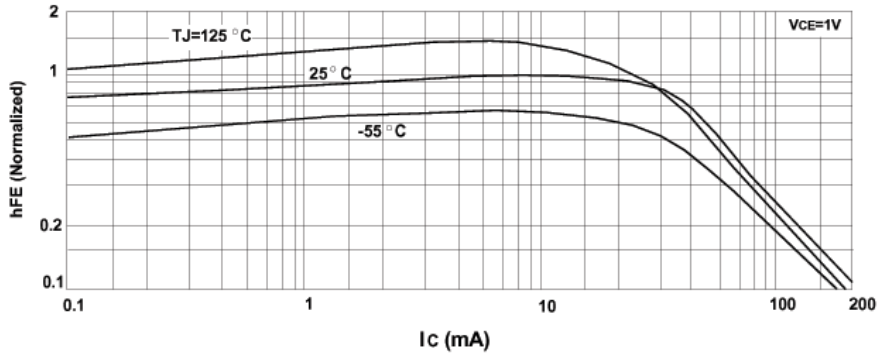


1. Emitter 2. Base 3. Collector  
TO-92 Plastic Package

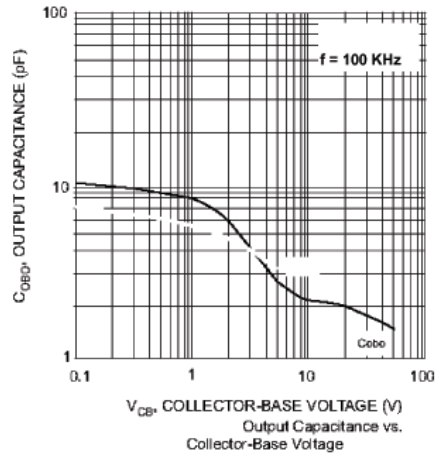
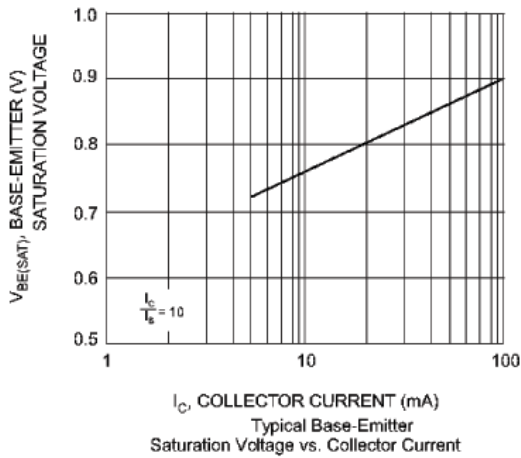
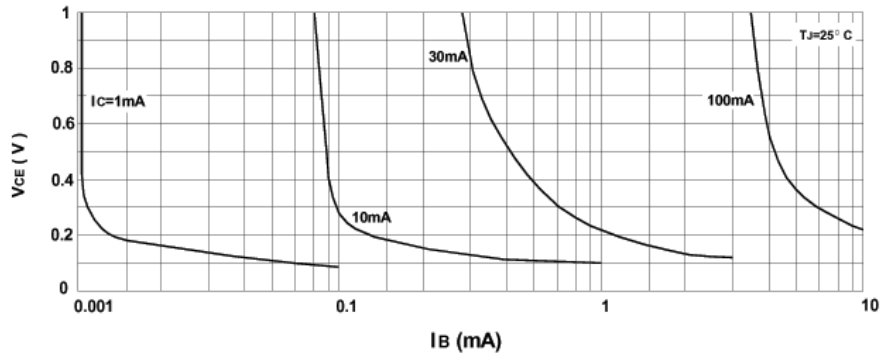
**Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)**

Parameter	Symbol	Value	Unit
Collector Base Voltage	-V <sub>CBO</sub>	40	V
Collector Emitter Voltage	-V <sub>CEO</sub>	40	V
Emitter Base Voltage	-V <sub>EBO</sub>	6	V
Collector Current	-I <sub>C</sub>	200	mA
Power Dissipation	P <sub>tot</sub>	625	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 150	°C

DC Current Gain



Collector Saturation Region



**Characteristics at  $T_a = 25\text{ }^\circ\text{C}$** 

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 1\text{ V}$ , $-I_C = 0.1\text{ mA}$	2N3905	$h_{FE}$	30	-
	2N3906	$h_{FE}$	60	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 1\text{ mA}$	2N3905	$h_{FE}$	40	-
	2N3906	$h_{FE}$	80	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 10\text{ mA}$	2N3905	$h_{FE}$	50	150
	2N3906	$h_{FE}$	100	300
at $-V_{CE} = 1\text{ V}$ , $-I_C = 50\text{ mA}$	2N3905	$h_{FE}$	30	-
	2N3906	$h_{FE}$	60	-
at $-V_{CE} = 1\text{ V}$ , $-I_C = 100\text{ mA}$	2N3905	$h_{FE}$	15	-
	2N3906	$h_{FE}$	30	-
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	50	nA
Emitter Base Cutoff Current at $-V_{EB} = 6\text{ V}$	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	-	V
Collector Emitter Breakdown Voltage at $-I_C = 1\text{ mA}$	$-V_{(BR)CEO}$	40	-	V
Emitter Base Breakdown Voltage at $-I_E = 10\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$	-	0.25	V
	$-V_{CE(sat)}$	-	0.4	
Base Emitter Saturation Voltage at $-I_C = 10\text{ mA}$ , $-I_B = 1\text{ mA}$ at $-I_C = 50\text{ mA}$ , $-I_B = 5\text{ mA}$	$-V_{BE(sat)}$	-	0.85	V
	$-V_{BE(sat)}$	-	0.95	
Gain Bandwidth Product at $-V_{CE} = 20\text{ V}$ , $-I_C = 10\text{ mA}$ , $f = 100\text{ MHz}$	2N3905	$f_T$	200	-
	2N3906		250	-
Collector Base Capacitance at $-V_{CB} = 5\text{ V}$ , $f = 100\text{ KHz}$	$C_{ob}$	-	4.5	pF
Delay Time at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$	$t_d$	-	35	ns
Rise Time at $-V_{CC} = 3\text{ V}$ , $-V_{BE} = 0.5\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = 1\text{ mA}$	$t_r$	-	35	ns
Storage Time at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$	$t_s$	-	225	ns
Fall Time at $-V_{CC} = 3\text{ V}$ , $-I_C = 10\text{ mA}$ , $-I_{B1} = I_{B2} = 1\text{ mA}$	$t_f$	-	75	ns